HAMAMATSU
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Photodiode arrays with amplifiers

S11865-64/-128/-256
S11866-64-02/-128-02

Photodiode arrays combined with signal processing IC

The S11865/S11866 series are Si photodiode arrays combined with a signal processing IC chip. X-ray tolerance has been improved compared to the previous products (S8865/S8866 series). The signal processing IC chip is formed by CMOS process and incorporates a timing generator, shift register, charge amplifier array, clamp circuit and hold circuit, making the external circuit configuration simple. A long, narrow image sensor can also be configured by arranging multiple arrays in a row. For X-ray detection applications, types with phosphor sheet affixed on the photosensitive area are also available.

Features

- **Data rate: 1 MHz max.**
- **Element pitch: 5 types available**
  S11865-64: 0.8 mm pitch × 64 ch
  S11865-128: 0.4 mm pitch × 128 ch
  S11865-256: 0.2 mm pitch × 256 ch
  S11866-64-02: 1.6 mm pitch × 64 ch
  S11866-128-02: 0.8 mm pitch × 128 ch
- **5 V power supply operation**
- **Simultaneous integration by using a charge amplifier array**
- **Sequential readout with a shift register**
- **Low dark current due to zero-bias photodiode operation**
- **Integrated clamp circuit allows low noise and wide dynamic range**
- **Integrated timing generator allows operation at two different pulse timings**
- **Types with phosphor sheet affixed on the photosensitive area are available for X-ray detection (S11865-64G/-128G/-256G, S11866-64G-02/-128G-02)**

Applications

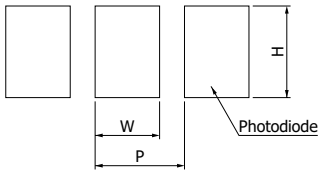
- **Long and narrow line sensors**
- **Line sensors for X-ray detection**

Structure

Parameter	Symbol*1	S11865-64	S11865-128	S11865-256	S11866-64-02	S11866-128-02	Unit
Element pitch	P	0.8	0.4	0.2	1.6	0.8	mm
Element width	W	0.7	0.3	0.1	1.5	0.7	mm
Element height	H	0.8	0.6	0.3	1.6	0.8	mm
Number of elements	-	64	128	256	64	128	-
Effective photosensitive area length	-	51.2	51.2	51.2	102.4	102.4	mm
Board material	-	Glass epoxy					-

*1: Refer to following figure.

Enlarged drawing of photosensitive area



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Absolute maximum ratings (Ta=25 °C, unless otherwise noted)

Parameter	Symbol	Value	Unit
Supply voltage	Vdd	-0.3 to +6	V
Reference voltage	Vref	-0.3 to +6	V
Photodiode voltage	Vpd	-0.3 to +6	V
Gain selection terminal voltage	Vgain	-0.3 to +6	V
Master/slave selection voltage	Vms	-0.3 to +6	V
Clock pulse voltage	V(CLK)	-0.3 to +6	V
Reset pulse voltage	V(RESET)	-0.3 to +6	V
External start pulse voltage	V(EXTSP)	-0.3 to +6	V
Operating temperature*2	Topr	-5 to +60	°C
Storage temperature*2	Tstg	-10 to +70	°C

*2: No dew condensation
When there is a temperature difference between a product and the surrounding area in high humidity environment, dew condensation may occur on the product surface. Dew condensation on the product may cause deterioration in characteristics and reliability.
Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

Recommended terminal voltage (Ta=25 °C)

Parameter		Symbol	Min.	Typ.	Max.	Unit
Supply voltage		Vdd	4.75	5	5.25	V
Reference voltage		Vref	4	4.5	4.6	V
Photodiode voltage		Vpd	-	Vref	-	V
Gain selection terminal voltage	High gain	Vgain	Vdd - 0.25	Vdd	Vdd + 0.25	V
	Low gain		0	-	0.4	V
Master/slave selection voltage	High level*3	Vms	Vdd - 0.25	Vdd	Vdd + 0.25	V
	Low level*4		0	-	0.4	V
Clock pulse voltage	High level	V(CLK)	3.3	Vdd	Vdd + 0.25	V
	Low level		0	-	0.4	V
Reset pulse voltage	High level	V(RESET)	3.3	Vdd	Vdd + 0.25	V
	Low level		0	-	0.4	V
External start pulse voltage	High level	V(EXTSP)	Vdd - 0.25	Vdd	Vdd + 0.25	V
	Low level		0	-	0.4	V

*3: Parallel
*4: Serial at 2nd or later stages

Electrical characteristics [Ta=25 °C, Vdd=5 V, V(CLK)=V(RESET)=5 V]

Parameter		Symbol	Min.	Typ.	Max.	Unit
Clock pulse frequency*5		f(CLK)	40	-	4000	kHz
Line rate*6	S11865-64, S11866-64-02	LR	-	-	14678	lines/s
	S11865-128, S11866-128-02		-	-	7568	
	S11865-256		-	-	3844	
Output impedance		Zo	-	3	-	kΩ
Current consumption	S11865-64, S11866-64-02	Ic	-	16	-	mA
	S11865-128, S11866-128-02		-	30	-	
	S11865-256		-	60	-	
Charge amp feedback capacitance	High gain	Cf	-	0.5	-	pF
	Low gain		-	1	-	

*5: Video data rate is 1/4 of clock pulse frequency f(CLK).
*6: The values depend on the clock pulse frequency.

Electrical and optical characteristics [Ta=25 °C, Vdd=5 V, V(CLK)=V(RESET)=5 V, Vgain=5 V (High gain), 0 V (Low gain)]

S11865-64/-128/-256

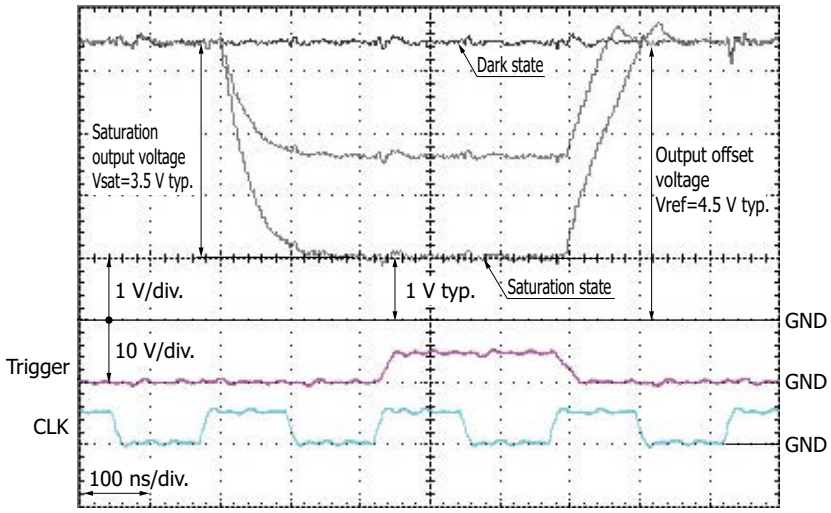
Parameter		Symbol	S11865-64			S11865-128			S11865-256			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
Spectral response range		λ	200 to 1000			200 to 1000			200 to 1000			nm
Peak sensitivity wavelength		λp	-	720	-	-	720	-	-	720	-	nm
Dark output voltage*7	High gain	Vd	-	0.01	0.2	-	0.01	0.2	-	0.01	0.2	mV
	Low gain		-	0.005	0.1	-	0.005	0.1	-	0.005	0.1	
Saturation output voltage		Vsat	3.0	3.5	-	3.0	3.5	-	3.0	3.5	-	V
Saturation exposure*8	High gain	Esat	-	0.8	1.0	-	2.4	3.0	-	15	19	$mlx \cdot s$
	Low gain		-	1.6	2.0	-	4.8	6.0	-	30	37.5	
Photosensitivity	High gain	Sw	3520	4400	-	1200	1500	-	200	250	-	$V/lx \cdot s$
	Low gain		1760	2200	-	600	750	-	100	125	-	
Photoresponse nonuniformity*9		PRNU	-	-	±10	-	-	±10	-	-	±10	%
Noise*10	High gain	N	-	1.3	2.0	-	1.0	1.5	-	0.8	1.2	mV rms
	Low gain		-	0.7	1.1	-	0.6	0.9	-	0.5	0.75	
Output offset voltage*11		Voffset	-	Vref	-	-	Vref	-	-	Vref	-	V

S11866-64-02/-128-02

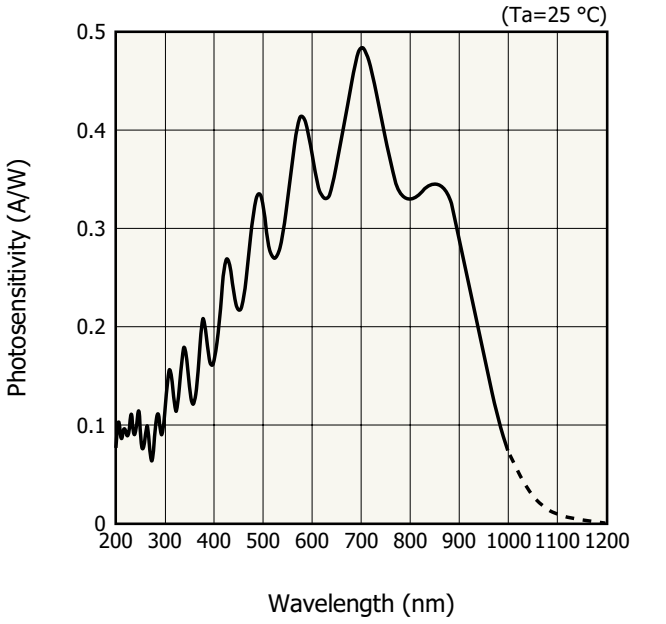
Parameter		Symbol	S11866-64-02			S11866-128-02			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Spectral response range		λ	200 to 1000			200 to 1000			nm
Peak sensitivity wavelength		λp	-	720	-	-	720	-	nm
Dark output voltage*7	High gain	Vd	-	0.01	0.2	-	0.01	0.2	mV
	Low gain		-	0.005	0.1	-	0.005	0.1	
Saturation output voltage		Vsat	3	3.5	-	3	3.5	-	V
Saturation exposure*8	High gain	Esat	-	0.2	0.25	-	0.8	1.0	$mlx \cdot s$
	Low gain		-	0.4	0.5	-	1.6	2.0	
Photosensitivity	High gain	Sw	14400	18000	-	3520	4400	-	$V/lx \cdot s$
	Low gain		7200	9000	-	1760	2200	-	
Photoresponse nonuniformity*9		PRNU	-	-	±10	-	-	±10	%
Noise*10	High gain	N	-	2.0	3.0	-	1.3	2.0	mV rms
	Low gain		-	1.1	1.7	-	0.7	1.1	
Output offset voltage*11		Voffset	-	Vref	-	-	Vref	-	V

*7: Integration time Ts=1 ms
*8: Measured with a 2856 K tungsten lamp.
*9: Photoresponse nonuniformity (PRNU) is the output nonuniformity that occurs when the photosensitive area is uniformly illuminated by light which is approx. 50% of the saturation level. PRNU is defined as follows:
PRNU = ΔX/X × 100 [%]
X: average output of all elements, ΔX: difference between X and the maximum or minimum output, whichever is larger.
*10: Measured with a video data rate of 50 kHz and Ts=1 ms in dark state.
*11: Video output is negative-going output with respect to the output offset voltage.

Output waveform of one element



Spectral response (typical example)



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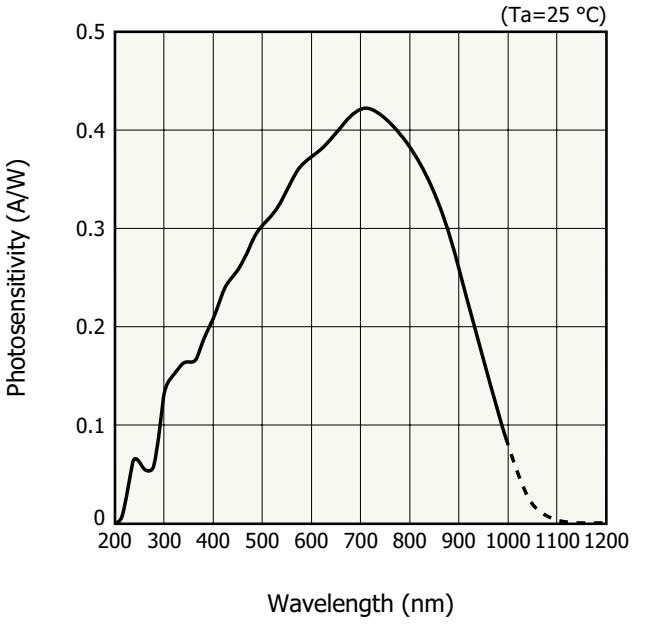
When silicone resin is applied (for attaching a fluorescent screen)



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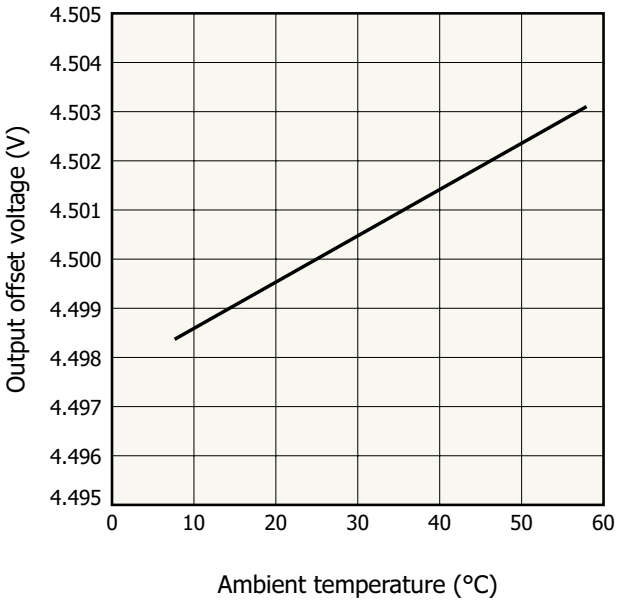
When the fluorescent screen is attached, the spectral response becomes smooth due to the effects of the adhesive resin.

Output offset voltage vs. ambient temperature (measurement example)



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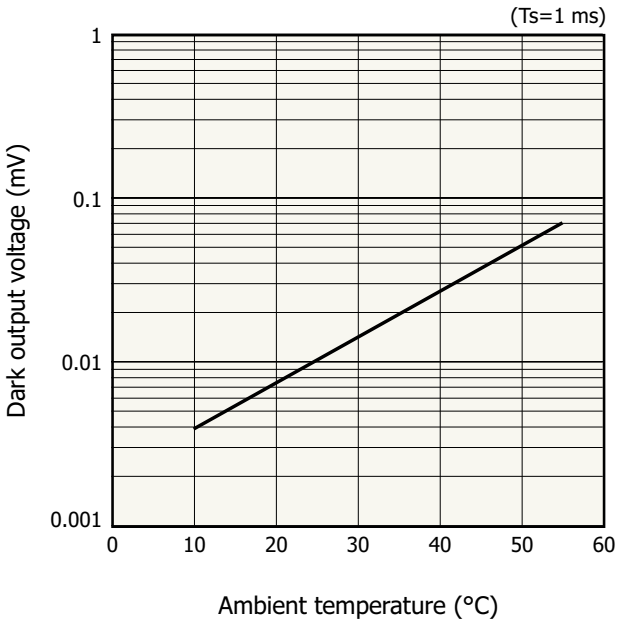
Dark output voltage vs. ambient temperature (typical example)



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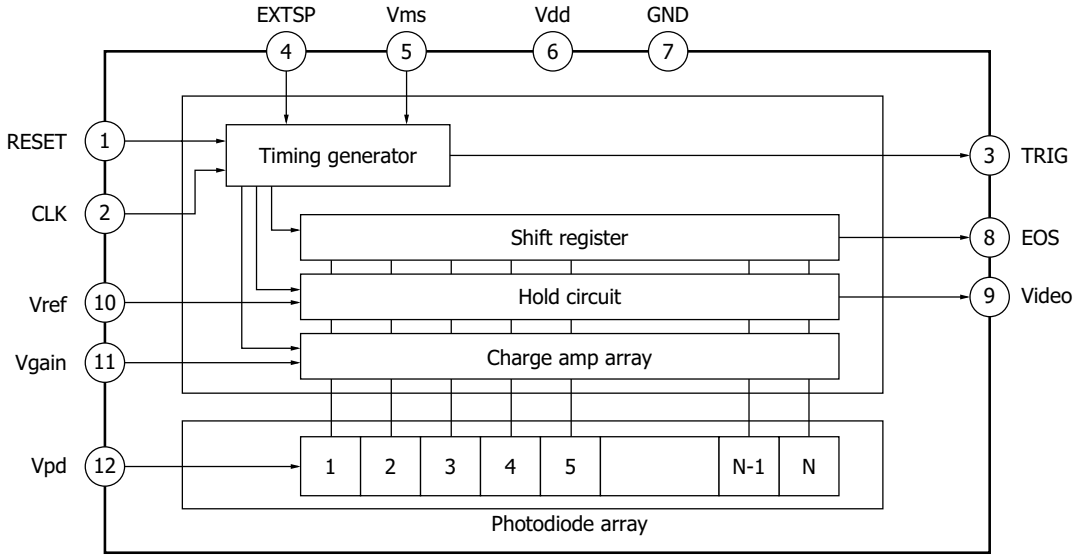
Block diagram

S11865-64/-128, S11866-64-02/-128-02



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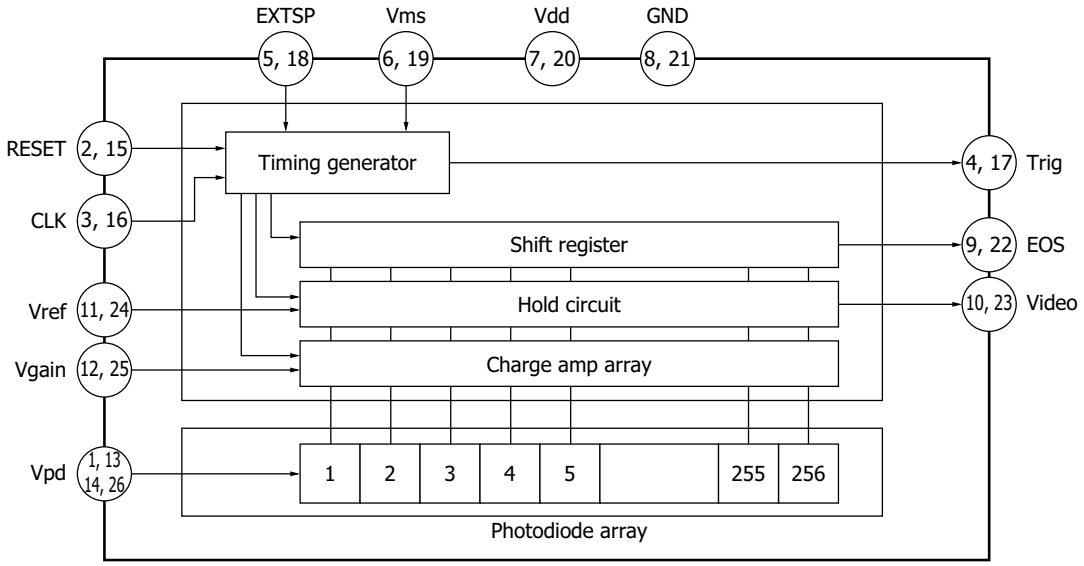
S11865-256



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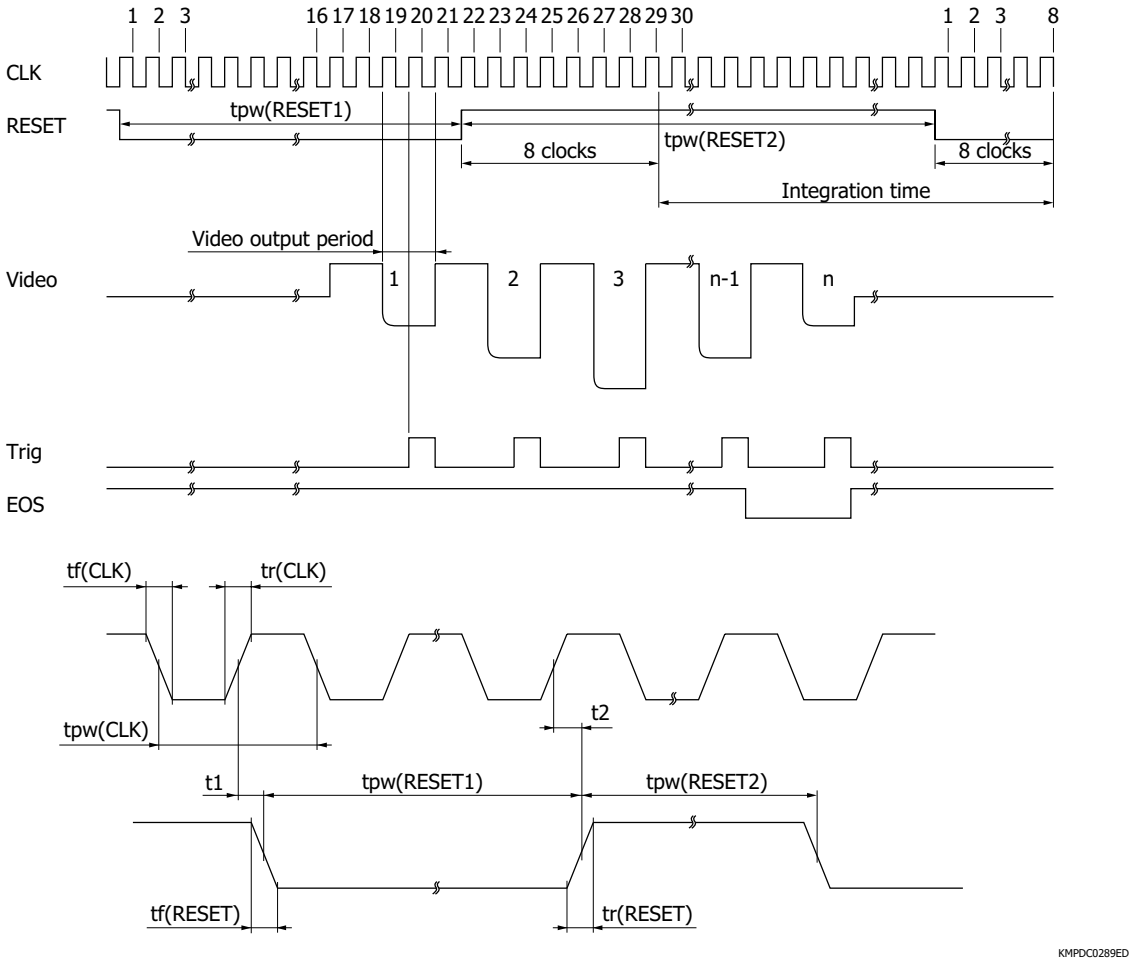
Timing chart

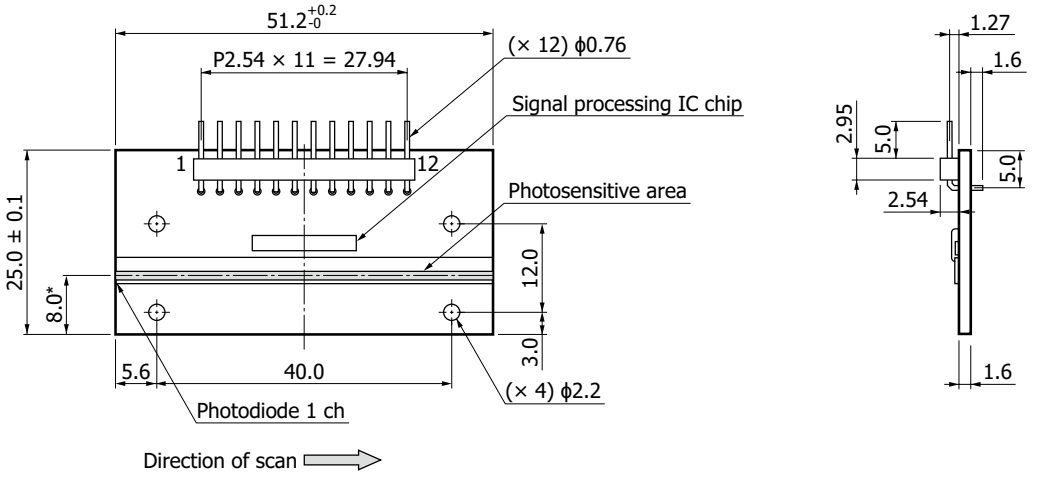


Parameter	Symbol	Min.	Typ.	Max.	Unit
Clock pulse width	tpw(CLK)	250	-	25000	ns
Clock pulse rise/fall times	tr(CLK), tf(CLK)	0	20	30	ns
Reset pulse width 1	tpw(RESET1)	21	-	-	CLK
Reset pulse width 2	tpw(RESET2)	20	-	-	CLK
Reset pulse rise/fall times	tr(RESET), tf(RESET)	0	20	30	ns
Clock pulse-reset pulse timing 1	t1	-20	0	20	ns
Clock pulse-reset pulse timing 2	t2	-20	0	20	ns

1. The internal timing circuit starts operation at the falling edge of CLK immediately after a RESET pulse goes Low.
2. When the falling edge of each CLK is counted as "1 clock", the video signal of the 1st channel appears between "18.5 clocks and 20.5 clocks". Subsequent video signals appear every 4 clocks.
3. The trigger pulse for the 1st channel rises at a timing of 19.5 clocks and then rises every 4 clocks. The rising edge of each trigger pulse is the recommended timing for data acquisition.
4. Signal charge integration time equals the High period of a RESET pulse. However, the charge integration does not start at the rise of a RESET pulse but starts at the fall of the 8th clock after the rise of the RESET pulse and ends at the fall of the 8th clock after the fall of the RESET pulse.
   After the RESET pulse next changes from High to Low, signals integrated within this period are sequentially read out as time-series signals by the shift register operation. The rise and fall of a RESET pulse must be synchronized with the rise of a CLK pulse, but the rise of a RESET pulse must be set outside the video output period. One cycle of RESET pulses cannot be set shorter than the time equal to "16.5 + 4 × N (number of elements)" clocks.
5. The video signal after an EOS signal output becomes a high impedance state, and the video output will be indefinite.

Dimensional outlines (unit: mm)

S11865-64/-128



Tolerance unless otherwise noted: ±0.2
* Distance from board bottom to photosensitive area center
Board: G10 glass epoxy
Connector: PRECI-DIP DURTAL 800-10-012-20-001101

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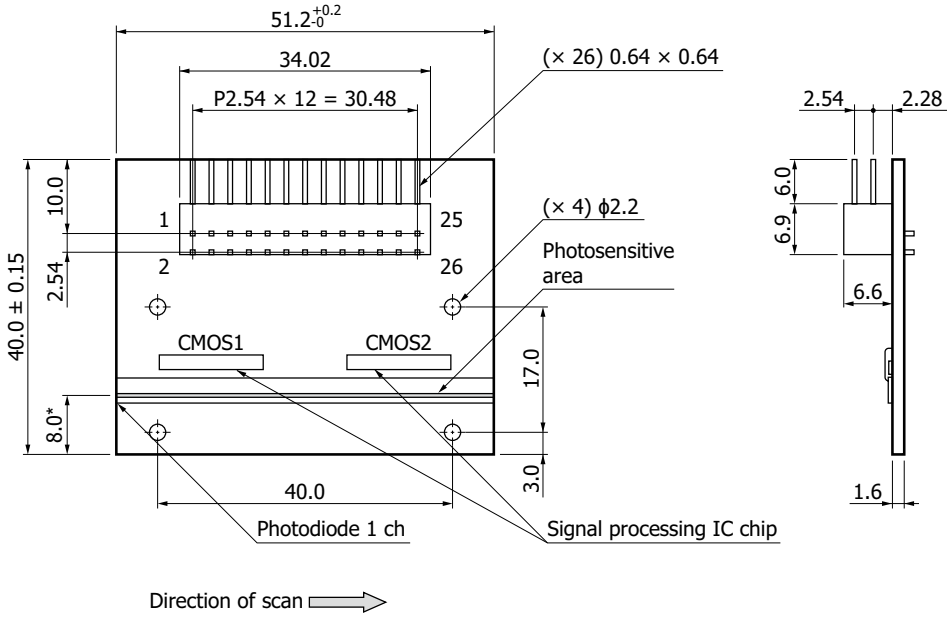
S11865-256



Tolerance unless otherwise noted: ±0.2
* Length from board bottom to photosensitive area center
Board: G10 glass epoxy
Connector: JAE (Japan Aviation Electronics Industry, Limited)
PS-26PE-D4LT1-PN1

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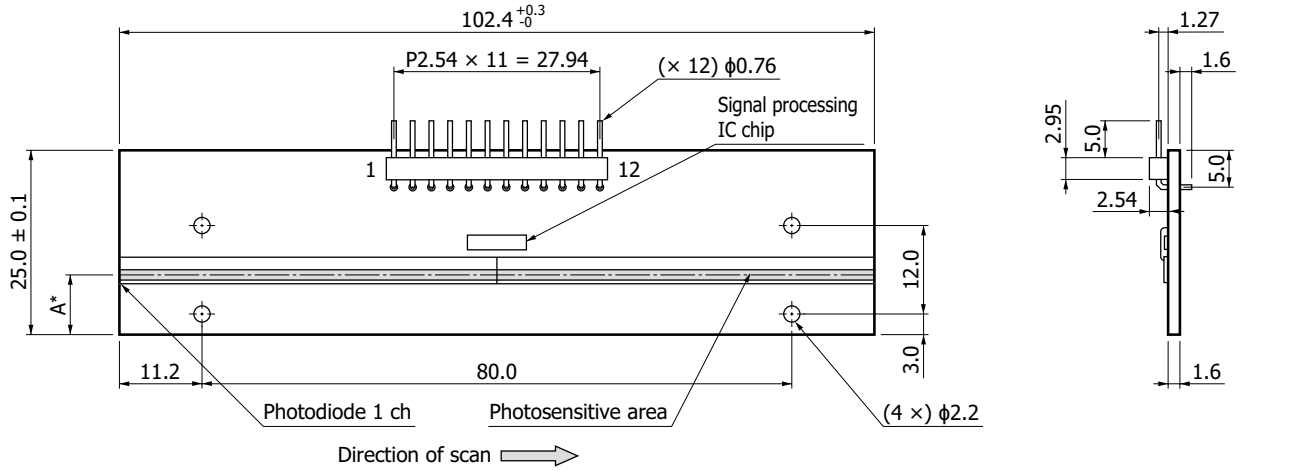
S11866-64-02/-128-02



Type no.	A
S11866-64-02	8.2
S11866-128-02	8.0

Tolerance unless otherwise noted: ±0.2
* Distance from board bottom to photosensitive area center
Board: G10 glass epoxy
Connector: PRECI-DIP DURTAL 800-10-012-20-001101

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Pin connections

S11865-64/-128, S11866-64-02/-128-02

Pin no.	Symbol	Name	Note
1	RESET	Reset pulse	Pulse input
2	CLK	Clock pulse	Pulse input
3	Trig	Trigger pulse	Positive-going pulse output
4	EXTSP	External start pulse	Pulse input
5	Vms	Master/slave selection supply voltage	Voltage input
6	Vdd	Supply voltage	Voltage input
7	GND	Ground	
8	EOS	End of scan	Negative-going pulse output
9	Video	Video output	Negative-going output with respect to Vref
10	Vref	Reference voltage	Voltage input
11	Vgain	Gain selection terminal voltage	Voltage input
12	Vpd	Photodiode voltage	Voltage input

S11865-256

Pin no.	CMOS1	Pin no.	CMOS2	Name	Note
1	Vpd	14	Vpd	Photodiode voltage	Voltage input
2	RESET	15	RESET	Reset pulse	Pulse input
3	CLK	16	CLK	Clock pulse	Pulse input
4	Trig	17	Trig	Trigger pulse	Positive-going pulse output
5	EXTSP	18	EXTSP	External start pulse	Pulse input
6	Vms	19	Vms	Master/slave selection voltage	Voltage input
7	Vdd	20	Vdd	Supply voltage	Voltage input
8	GND	21	GND	Ground	
9	EOS	22	EOS	End of scan	Negative-going pulse output
10	Video	23	Video	Video output	Negative-going output from Vref
11	Vref	24	Vref	Reference voltage	Voltage input
12	Vgain	25	Vgain	Gain selection voltage	Voltage input
13	Vpd	26	Vpd	Photodiode voltage	Voltage input

Gain selection terminal voltage setting

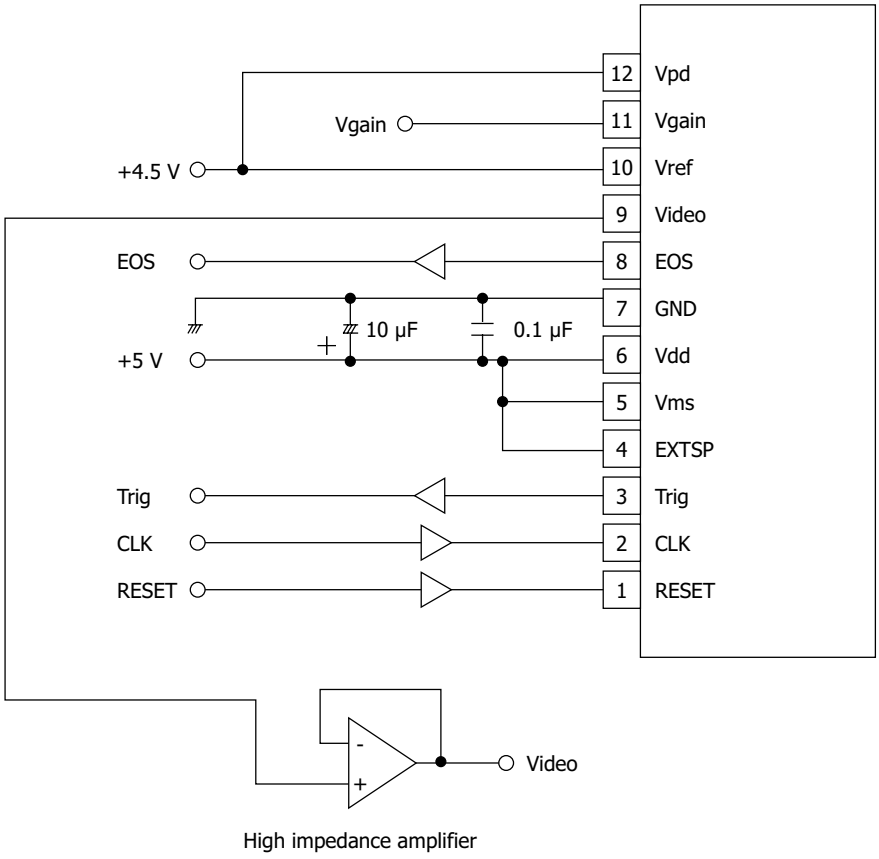
Vdd: High gain (Cf=0.5 pF) GND: Low gain (Cf=1 pF)

Setting for each readout method

S11865-64/-128, S11866-64-02/-128-02

Set to A in the table below in most cases.
To serially read out signals from two or more sensors linearly connected, set the 1st sensor to A and the 2nd or later sensors to B.
The CLK and RESET pulses should be shared with each sensor and the video output terminal of each sensor connected together.

■ Connection example (parallel readout)



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Setting	Readout method	Vms	EXTSP
A	All stages of parallel readout, serial readout at 1st sensor	Vdd	Vdd
B	Serial readout at 2nd and later sensors	GND	Preceding sensor EOS should be input

S11865-256

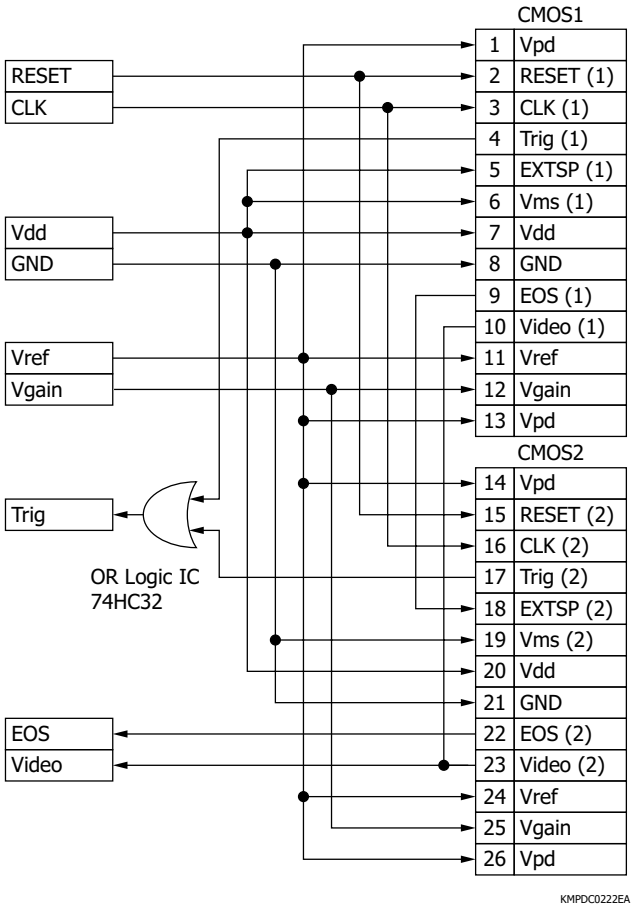
Signals of channels 1 through 126 are output from CMOS1, while signals of channels 129 through 256 are output from CMOS2. The following two readout methods are available.

(1) Serial readout method
CMOS1 and CMOS2 are connected in serial and the signals of channels 1 through 256 are sequentially read out from one output line. Set CMOS1 as in "A" in the table below, and set CMOS2 as in "B". CMOS1 and CMOS2 should be connected to the same CLK and RESET lines, and their video output terminals to one line.

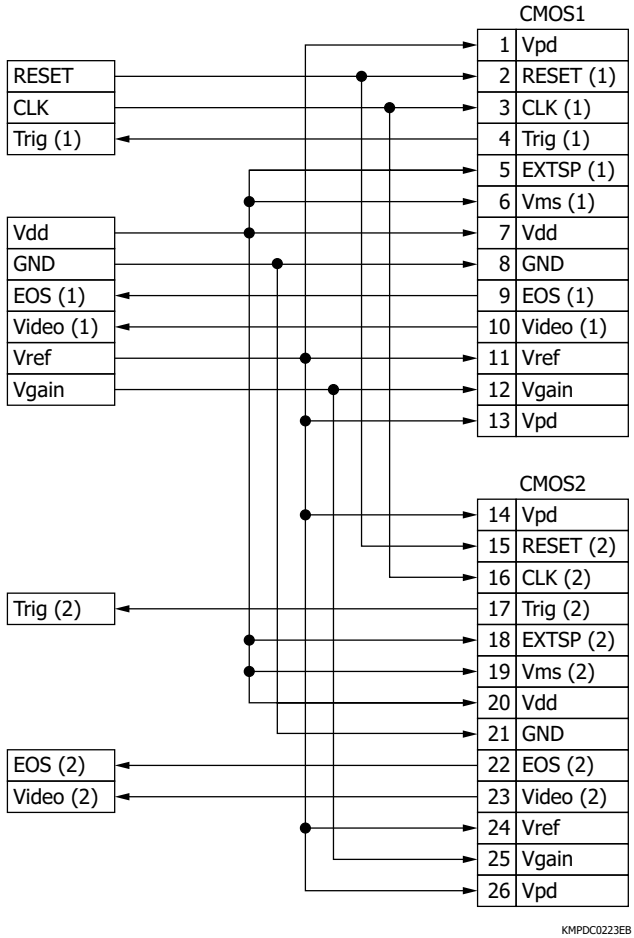
(2) Parallel readout method
128 channel signals are output in parallel respectively from the output lines of CMOS1 and CMOS2. Set both CMOS1 and CMOS2 as in "A" in the table below.

■ Connection examples

· Serial readout method



· Parallel readout method



Setting	Vms	EXTSP
A	Vdd	Vdd
B	GND	Preceding sensor EOS should be input

Readout circuit

Check that pulse signals meet the required pulse conditions before supplying them to the input terminals.
Video output should be amplified by an operational amplifier that is connected close to the sensor.

Precautions for use

(1) The signal processing IC chip is protected against static electricity. However, in order to prevent possible damage to the IC chip, take electrostatic countermeasures such as grounding yourself, as well as workbench and tools. Also protect the IC chip from surge voltages from peripheral equipment.

(2) Gold wires for wire bonding are very thin, so they easily break if subjected to mechanical stress. The signal processing IC chip and wire bonding section are covered with resin for protection. However, never touch these portions. Excessive force, if applied, may break the wires or cause malfunction.
Blow air to remove dust or debris if it gets on the protective resin. Never wash them with solvent.
Signals may not be obtained if dust or debris is left or a scratch is made on the protective resin, or the signal processing IC chip or photodiode array chip is nicked.

(3) The photodiode array characteristics may deteriorate when operated at high humidity, so put it in a hermetically sealed enclosure or case.
When installing the photodiode array on a board, be careful not to cause the board to warp.

Related information

www.hamamatsu.com/sp/ssd/doc_en.html

■ Precautions
· Disclaimer
· Precautions / Unsealed products
· Precautions / Image sensors

Information described in this material is current as of September 2025.
Product specifications are subject to change without prior notice due to improvements or other reasons. This document has been carefully prepared and the information contained is believed to be accurate. In rare cases, however, there may be inaccuracies such as text errors. Before using these products, always contact us for the delivery specification sheet to check the latest specifications.
The product warranty is valid for one year after delivery and is limited to product repair or replacement for defects discovered and reported to us within that one year period. However, even if within the warranty period we accept absolutely no liability for any loss caused by natural disasters or improper product use.
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